



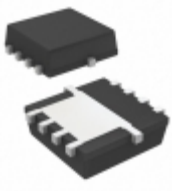
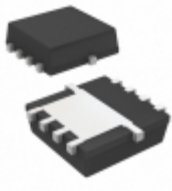

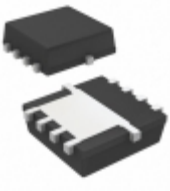

	<h2>SI7703EDN-T1-E3</h2>
	<p><b>Hersteller-Teilenummer:</b> SI7703EDN-T1-E3</p> <p><b>Hersteller / Marke:</b> Electro-Films (EFI) / Vishay</p> <p><b>Teil der Beschreibung:</b> MOSFET P-CH 20V 4.3A 1212-8</p> <p><b>Datenblätter:</b>  <a href="#">SI7703EDN-T1-E3.pdf</a></p> <p><b>RoHS Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 54740 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

### Spezifikationen

Teilenummer	SI7703EDN-T1-E3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 20V 4.3A 1212-8
Kategorie	<a href="#">Diskrete Halbleiterprodukte</a> > <a href="#">Transistoren-FETs</a> ,
Teilstatus	54740 pcs Stock
Hersteller Standard Vorlaufzeit	49 Weeks
detaillierte Beschreibung	P-Channel 20V 4.3A (Ta) 1.3W (Ta) Surface Mount
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® 1212-8
Supplier Device-Gehäuse	PowerPAK® 1212-8
Verlustleistung (max)	1.3W (Ta)
Typ FET	P-Channel
FET-Merkmal	Schottky Diode (Isolated)
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	4.3A (Ta)
Rds On (Max) @ Id, Vgs	48 mOhm @ 6.3A, 4.5V
VGS (th) (Max) @ Id	1V @ 800µA
Gate Charge (Qg) (Max) @ Vgs	18nC @ 4.5V
Antriebsspannung (Max Rds On, Min Rds On)	1.8V, 4.5V
Vgs (Max)	±12V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI7703EDN-T1-E3TR

SI7703EDN-T1-E3 ist neu im Original, Suche SI7703EDN-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7703EDN-T1-E3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI7703EDN-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p><b>SI7703EDN</b> QFN-8 SI7703EDN QFN-8</p>	 <p><b>SI7703EDN-T1</b> VISHAY SI7703EDN-T1 VISHAY</p>	 <p><b>SI7703EDN-T1-E3</b> SILICONE SI7703EDN-T1-E3 SILICONE</p>	 <p><b>SI7703EDN-T1-GE3</b> Vishay / Siliconix MOSFET P-CH 20V 4.3A 1212-8 PPAK</p>
 <p><b>SI7703EDN-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET P-CH 20V 4.3A 1212-8 PPAK</p>	 <p><b>SI7705DN-T1</b> VISHAY SI7705DN-T1 VISHAY</p>	 <p><b>SI7703EDN-T1-E3</b> Vishay / Siliconix MOSFET P-CH 20V 4.3A 1212-8</p>	 <p><b>SI7703DN</b> VISHAY SI7703DN VISHAY</p>

### heiße Teile

Mehr

SI7661CSA	SI7661CSA+	SI7668ADP-T1-E3	SI7668ADP-T1-E3	SI7668ADP-T1-GE3
SI7668ADP-T1-GE3	SI7674DP	SI7674DP-T1-GE3	SI7674DP-T1-GE3	SI7682DP
SI7682DP-T1-E3	SI7682DP-T1-E3	SI7682DP-T1-GE3	SI7682DP-T1-GE3	SI7682DY-T1-GE3
SI7684DP-T1-GE3	SI7686DP	SI7686DP-T1	SI7686DP-T1-E3	SI7686DP-T1-E3
SI7686DP-T1-GE3	SI7686DP-T1-GE3	SI7703DN	SI7703EDN	SI7703EDN-T1
SI7703EDN-T1-E3	SI7703EDN-T1-GE3	SI7703EDN-T1-GE3	SI7703EDN-TI-E3	SI7705DN
SI7705DN-T1	SI7705DN-T1-E3	SI7716ADN	SI7716ADN-T1-E3	SI7716ADN-T1-GE3
SI7716ADN-T1-GE3	SI7716ADN-TI-GE3	SI7716DN-T1-GE3	SI7720DN-T1-E3	SI7720DN-T1-GE3
SI7720DN-T1-GE3	SI7726DN	SI7726DN-T1-E3	SI7726DN-T1-GE3	SI7726DN-T1-GE3
SI7732DP-T1-GE3	SI7738DP	SI7738DP-T1-3	SI7738DP-T1-E3	SI7738DP-T1-E3

Contact us: [Info@Y-IC.com](mailto:Info@Y-IC.com)

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